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(71) Applicant: **MERCK PATENT GMBH** [DE/DE]; Frank-
furter Straße 250, 64293 Darmstadt (DE).

(72) Inventors: **LI, Zhong**; c/o EMD Performance Materials
Corp., 70 Meister Avenue, Branchburg, New Jersey 08876
(US). **WU, Hengpeng**; c/o EMD Performance Materials
Corp., 70 Meister Avenue, Branchburg, New Jersey 08876
(US). **CHEN, Chunwei**; c/o EMD Performance Materi-
als Corp., 70 Meister Avenue, Branchburg, New Jersey
08876 (US). **LIU, Weihong**; c/o EMD Performance Mate-
rials Corp., 70 Meister Avenue, Branchburg, New Jersey
08876 (US). **CHEN, Hung-Yang**; c/o EMD Performance
Materials Corp., 70 Meister Avenue, Branchburg, New Jer-
sey 08876 (US).

(74) Agent: **RIPPEL, Hans Christoph**; Patentanwälte Isen-
bruck Bösl Hörschler PartG mbB, Seckenheimer Land-
straße 4, 68163 Mannheim (DE).

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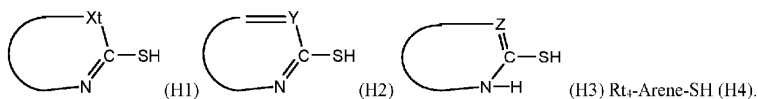
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(57) Abstract: One aspect of this invention is a photoresist composition comprising a thiol derivatives where the thiol moiety is attached to an SP² carbon which is part of ring which has structures (H1), (H2) (H3), or (H4), and where this thiol additive is present in a range of about 0.5 wt. % to about 3 wt. % of total solids. Another aspect of this invention is to use this photoresist composition on a metal substrate a patterned photoresist which is use as a etch mask in anisotropic wet chemical etching of the metal substate to produce a patterned metallic substrate. Yet Another aspect of this invention is a composition which comprises the above-described thiol derivatives in a spin casting solution and the process of treating a metal substrate which allows overlaid patterned photo resist to be used as an etch mask for wet chemical etching to affect anisotropic etching of the metal substate to also generate patterned metallic substate.

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